GaN and InP Chiplet Integration in CMOS Wafers for Millimeter-wave Front-ends

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This talk presents an overview of PseudolithIC's work developing RF integrated circuits that leverage foundry silicon wafers and compound semiconductor devices Demonstrated circuits, designed and assembled by PseudolithIC, highlight the combination of Gallium Nitride and Indium Phosphide devices in a silicon platform to optimize performance and lower product cost. The impact of the process on accelerating development timeline and enhancing system performance for defense and space applications will be discussed.